MMBTSC5343W

NPN Silicon Epitaxial Planar Transistor

for general small signal amplifier applications.

The transistor is subdivided into four groups, O, Y, G and L, according to its DC current gain.



1.Base 2.Emitter 3.Collector SOT-323 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	Ι _C	150	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 +150	°C

Characteristics at T_{amb} = 25 °C

Parameter		Symbol	Min.	Max.	Unit
DC Current Gain at V_{CE} = 6 V, I_C = 2 mA Current Gain Group	O Y G L	h _{FE} h _{FE} h _{FE} h _{FE}	70 120 200 300	140 240 400 700	- - - -
Collector Base Breakdown Voltage at $I_c = 100 \ \mu A$		V _{(BR)CBO}	60	-	V
Collector Emitter Breakdown Voltage at $I_c = 1 \text{ mA}$		V _{(BR)CEO}	50	-	V
Emitter Base Breakdown Voltage at I _E = 10 μA		V _{(BR)EBO}	5	-	V
Collector Cutoff Current at V _{CB} = 60 V		I _{CBO}	-	0.1	μA
Emitter Cutoff Current at V _{EB} = 5 V		I _{EBO}	-	0.1	μA
Collector Emitter Saturation Voltage at I_c = 100 mA, I_B = 10 mA		V _{CE(sat)}	-	0.25	V
Transition Frequency at V_{CE} = 10 V, I_C = 1 mA		f⊤	80	-	MHz
Collector Output Capacitance at V_{CB} = 10 V, f = 1 MHz		C _{OB}	-	3.5	pF
Noise Figure at V _{CE} = 6 V, I _C = 0.1 mA, f = 1 KHz, R _G = 10 K Ω		NF	-	10	dB



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

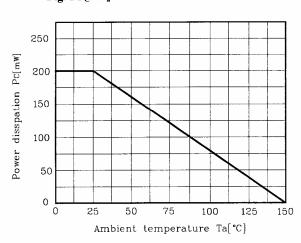


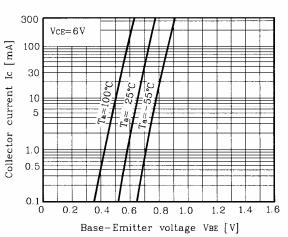
Dated : 30/03/2006

MMBTSC5343W

Fig. 1 P_C – T_a

Fig. 2 $I_{\rm C}$ -V_{BE}







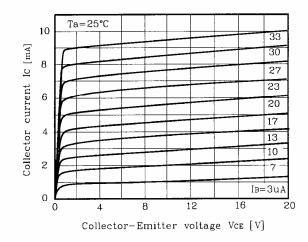


Fig. 5 V_{CE(sat)}-I_C

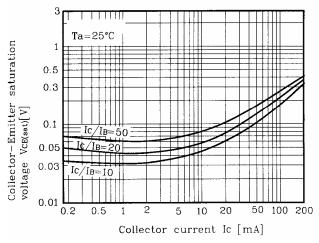
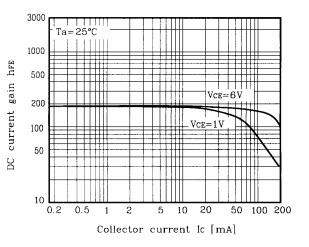


Fig. 4 $h_{FE}\mathchar`-I_C$









Dated : 30/03/2006